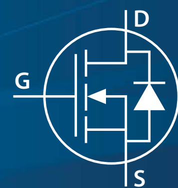
EPC2024 – Enhancement Mode Power Transistor

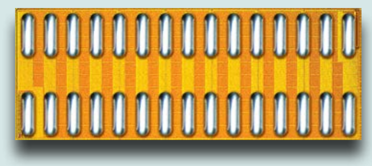
V_{DS} , 40 V
$R_{DS(on)}$, 1.5 mΩ
I_D , 90 A



EFFICIENT POWER CONVERSION

RoHS Halogen-Free

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.



EPC2024 eGaN® FETs are supplied only in passivated die form with solder bumps.
Die Size: 6.05 mm x 2.3 mm

- High Speed DC-DC Conversion
- Motor Drive
- Industrial Automation
- Synchronous Rectification
- Inrush Protection
- Point-of-Load (POL) Converters

Maximum Ratings			
PARAMETER		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage (Continuous)	40	V
	Drain-to-Source Voltage (up to 10,000 5 ms pulses at 150°C)	48	
I_D	Continuous (T_A = 25°C, $R_{θJA}$ = 6°C/W)	90	A
	Pulsed (25°C, T_{PULSE} = 300 µs)	560	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	-40 to 150	°C
T_{STG}	Storage Temperature	-40 to 150	

Thermal Characteristics			
PARAMETER		TYP	UNIT
$R_{θJC}$	Thermal Resistance, Junction-to-Case	0.4	°C/W
$R_{θJB}$	Thermal Resistance, Junction-to-Board	1.1	
$R_{θJA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	42	

Note 1: $R_{θJA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details.

Static Characteristics (T_J = 25°C unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 1.1mA	40			V
I_{DSS}	Drain-Source Leakage	V_{GS} = 0 V, V_{DS} = 32 V		0.1	0.9	mA
I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		1	9	mA
	Gate-to-Source Reverse Leakage	V_{GS} = -4 V		0.1	0.9	mA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 19 mA	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 37 A		1.2	1.5	mΩ
V_{SD}	Source-Drain Forward Voltage	I_S = 0.5 A, V_{GS} = 0 V		1.8		V

All measurements were done with substrate connected to source.

Dynamic Characteristics (T_J = 25°C unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	V_{DS} = 20 V, V_{GS} = 0 V		1920	2300	pF
C_{OSS}	Output Capacitance			1620	2430	
C_{RSS}	Reverse Transfer Capacitance			29		
$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	V_{DS} = 0 to 20 V, V_{GS} = 0 V		2050		
$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			2240		
R_G	Gate Resistance			0.3		Ω
Q_G	Total Gate Charge	V_{DS} = 20 V, V_{GS} = 5 V, I_D = 37 A		18	24	nC
Q_{GS}	Gate-to-Source Charge	V_{DS} = 20 V, I_D = 37 A		5.1		
Q_{GD}	Gate-to-Drain Charge			2.4		
$Q_{G(TH)}$	Gate Charge at Threshold			3.8		
Q_{OSS}	Output Charge	V_{DS} = 20 V, V_{GS} = 0 V		45	68	
Q_{RR}	Source-Drain Recovery Charge			0		

All measurements were done with substrate connected to source.
Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.
Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.

Figure 1: Typical Output Characteristics at 25°C

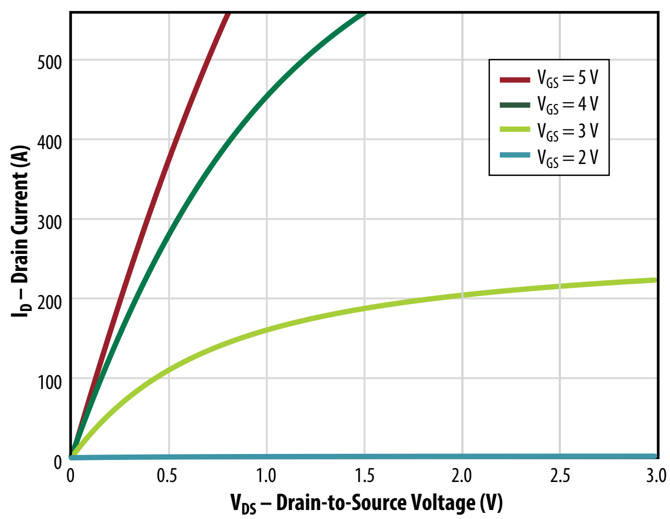


Figure 2: Transfer Characteristics

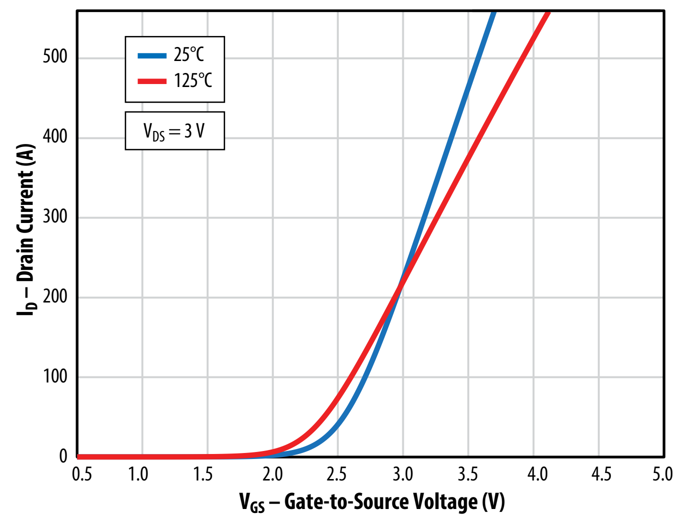


Figure 3: $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

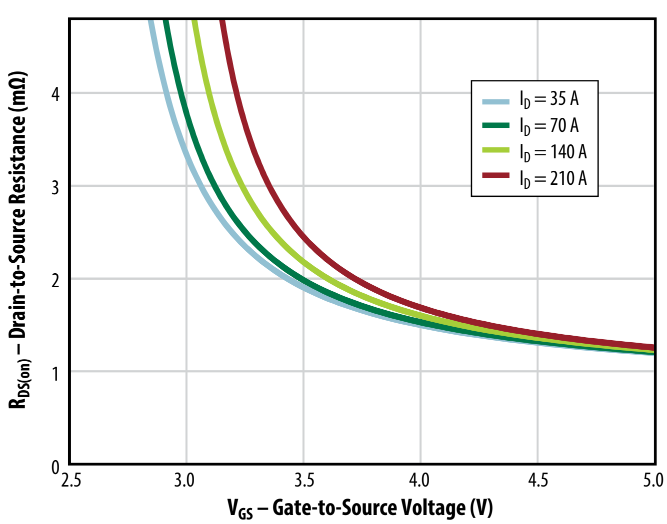


Figure 4: $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

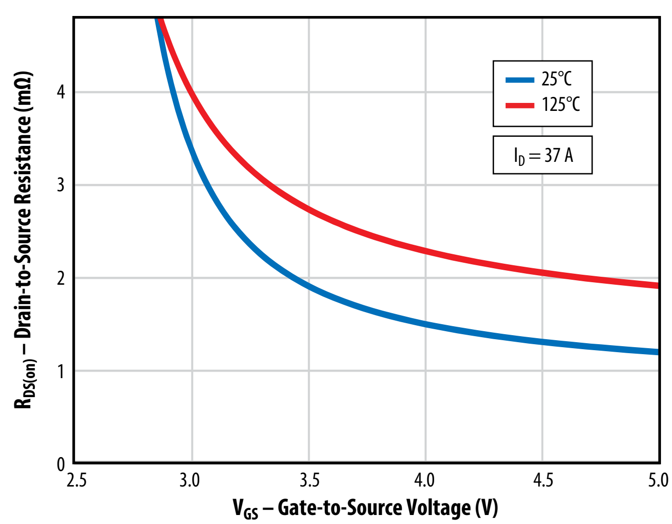


Figure 5a: Capacitance (Linear Scale)

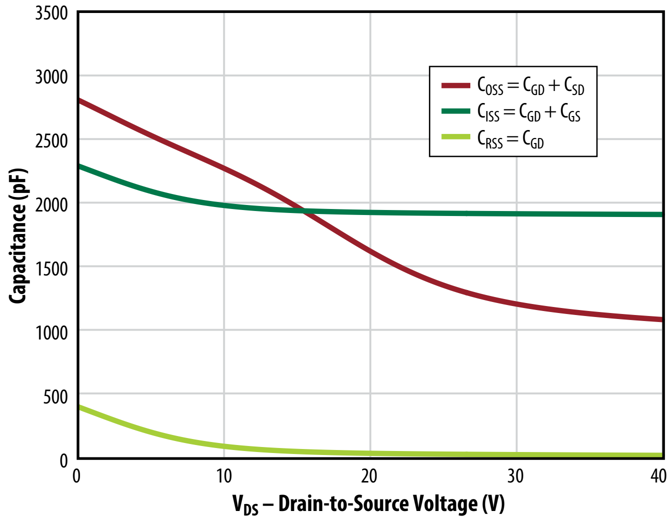


Figure 5b: Capacitance (Log Scale)

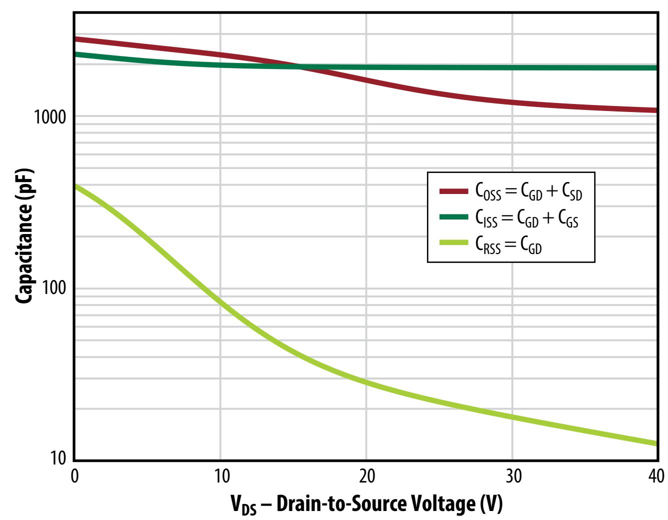


Figure 6: Gate Charge

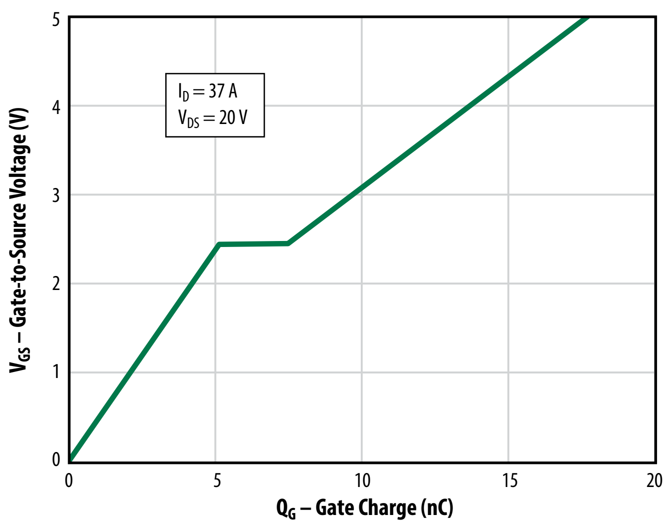


Figure 7: Reverse Drain-Source Characteristics

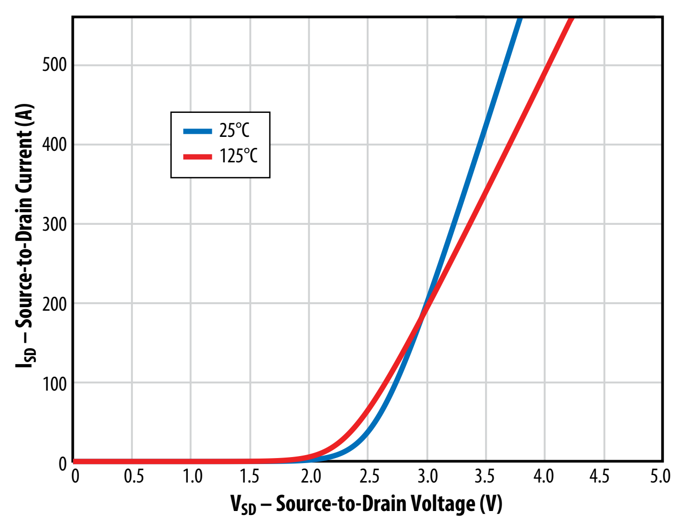


Figure 8: Normalized On-State Resistance vs. Temperature

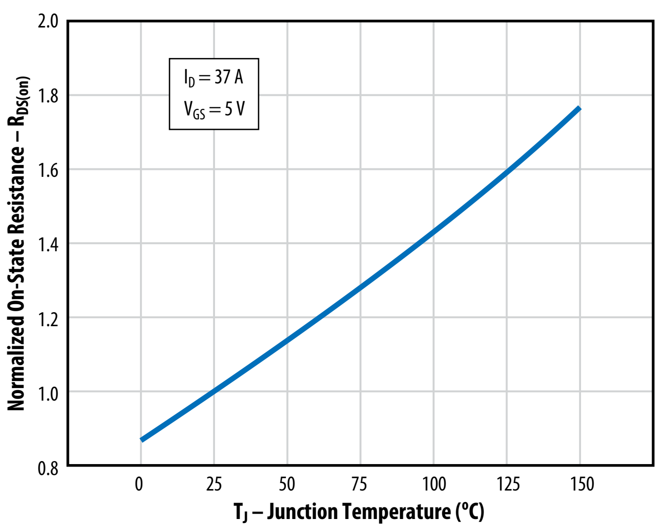
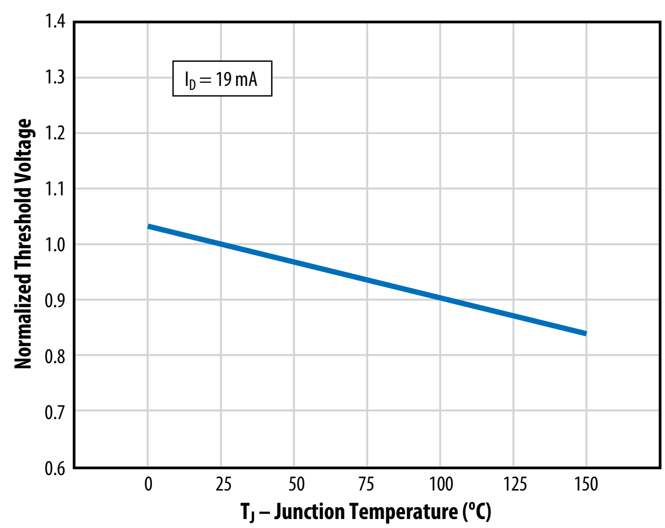


Figure 9: Normalized Threshold Voltage vs. Temperature



All measurements were done with substrate shortened to source.

Figure 10: Gate Leakage Current

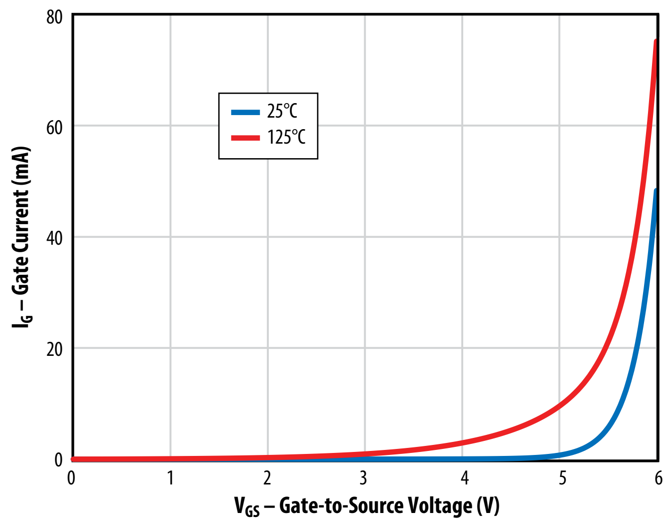
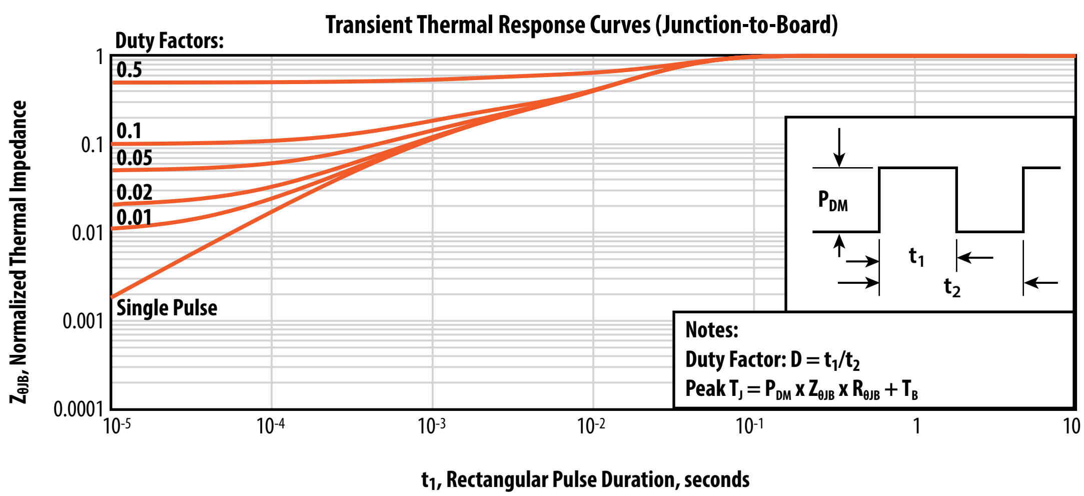


Figure 11: Transient Thermal Response Curves



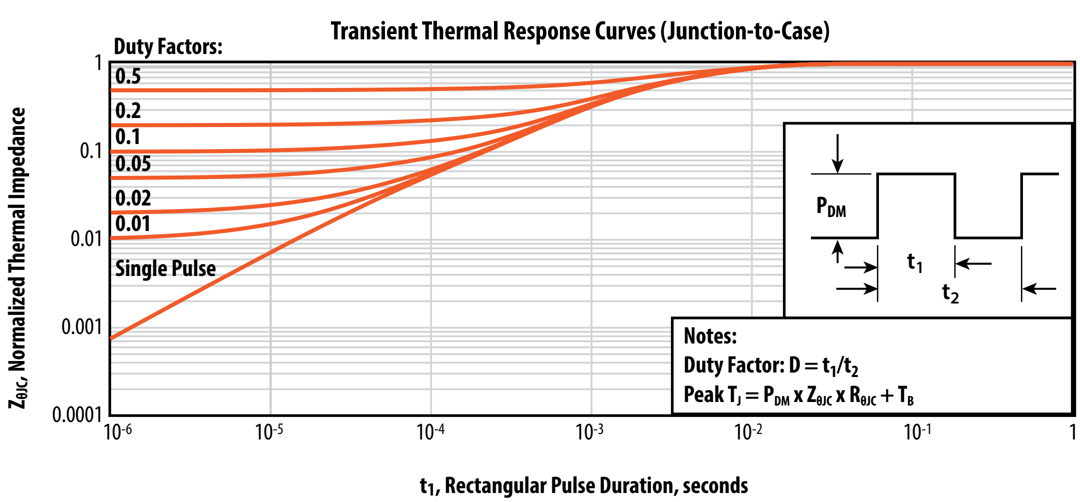
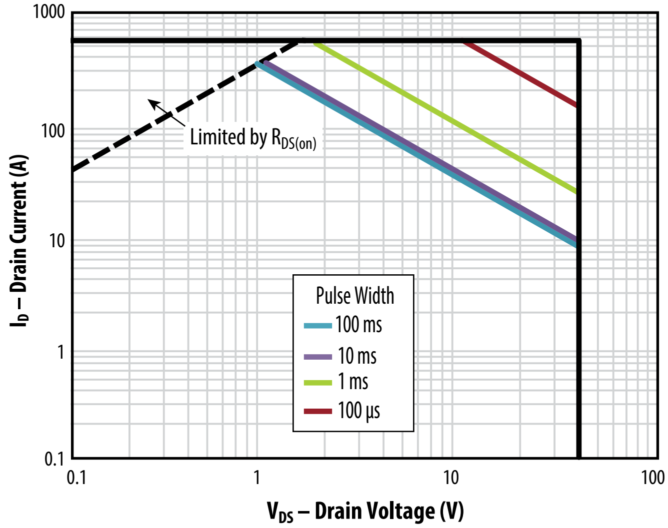
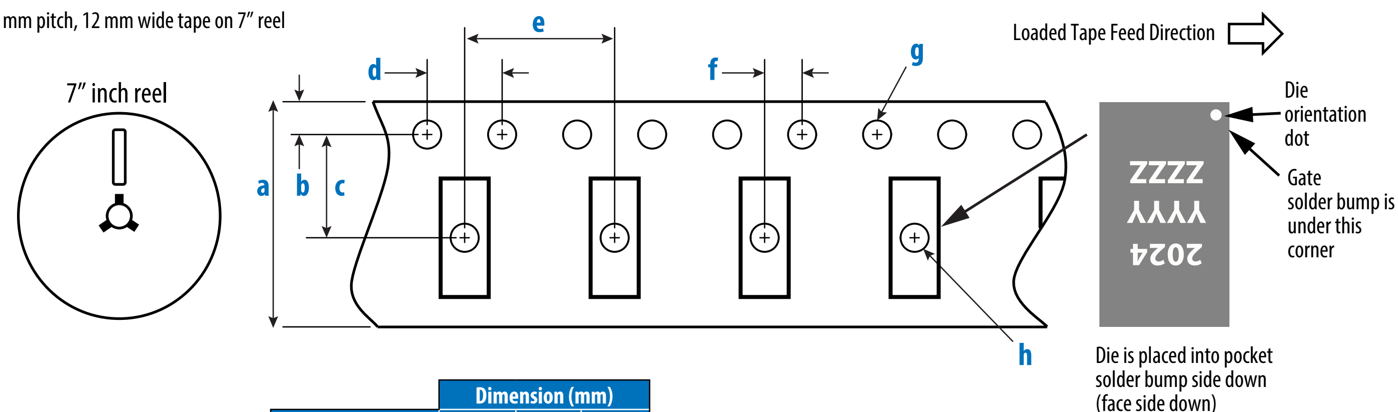


Figure 12: Safe Operating Area



TAPE AND REEL CONFIGURATION

8 mm pitch, 12 mm wide tape on 7″ reel

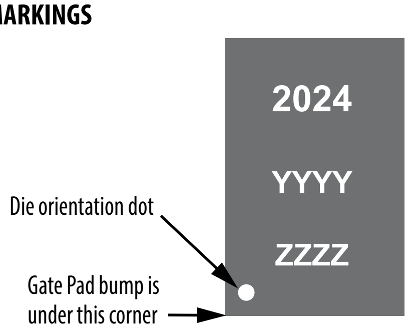


	Dimension (mm)		
EPC2024 (Note 1)	Target	MIN	MAX
a	12.00	11.90	12.30
b	1.75	1.65	1.85
c (Note 2)	5.50	5.45	5.55
d	4.00	3.90	4.10
e	8.00	7.90	8.10
f (Note 2)	2.00	1.95	2.05
g	1.50	1.50	1.60
h	1.50	1.50	1.75

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.

Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

DIE MARKINGS

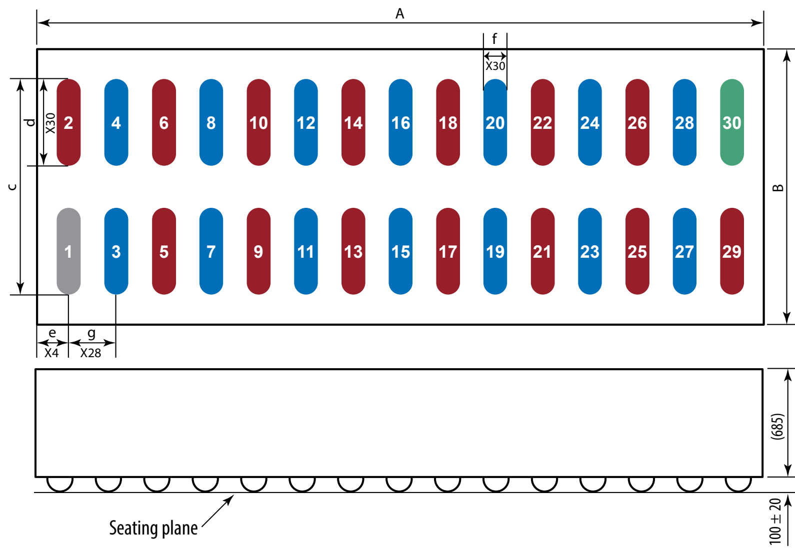


Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3
EPC2024	2024	YYYY	ZZZZ

DIE OUTLINE

Solder Bump View

Side View



DIM	Micrometers		
	MIN	Nominal	MAX
A	6020	6050	6080
B	2270	2300	2330
c	2047	2050	2053
d	717	720	723
e	210	225	240
f	195	200	205
g	400	400	400

Pad 1 is Gate;

Pads 2 ,5, 6, 9, 10, 13, 14, 17, 18, 21, 22, 25, 26, 29 are Source;

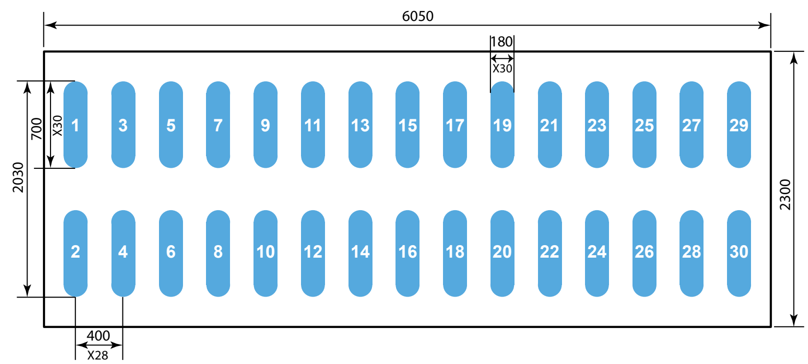
Pads 3, 4, 7, 8, 11, 12, 15, 16, 19, 20, 23, 24, 27, 28 are Drain;

Pad 30 is Substrate.*

*Substrate pin should be connected to Source

RECOMMENDED LAND PATTERN

(units in µm)



Land pattern is solder mask defined

Solder mask opening is 180 µm

It is recommended to have on-Cu trace PCB vias

Pad 1 is Gate;

Pads 2, 5, 6, 9,10,13,14, 17, 18, 21, 22, 25, 26, 29 are Source;

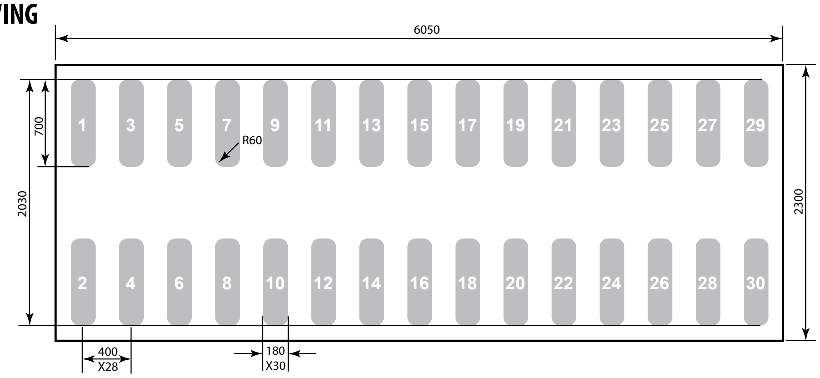
Pads 3, 4, 7, 8, 11, 12, 15, 16, 19, 20, 23, 24, 27, 28 are Drain;

Pad 30 is Substrate.*

*Substrate pin should be connected to Source

RECOMMENDED STENCIL DRAWING

(units in µm)



Recommended stencil should be 4 mil (100 µm) thick, must be laser cut, openings per drawing.

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at https://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx

Information subject to change without notice.
Revised May, 2022